

ACMSP2303T-HF

P-Channel
RoHS Device
Halogen Free



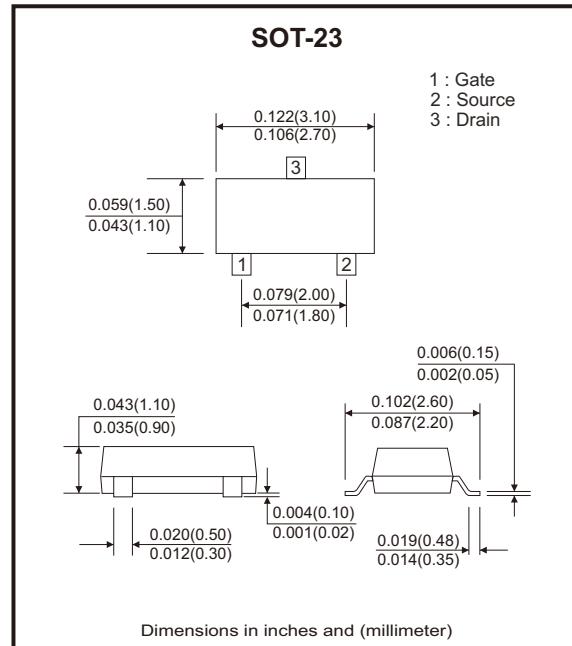
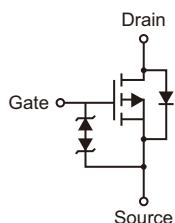
Features

- Electrostatic sensitive devices.
- V_{DS} (V) = -30V.
- I_D = -2.7A (V_{GS} = -10V)
- $R_{DS(ON)} < 190\text{m}\Omega$ (V_{GS} = -10V)
 $R_{DS(ON)} < 330\text{m}\Omega$ (V_{GS} = -4.5V)
- AEC-Q101 Qualified.

Mechanical data

- Case: SOT-23, molded plastic.

Circuit Diagram



Maximum Ratings (at $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DSS}	-30	V
Gate-source voltage	V_{GSS}	± 20	V
Continuous drain current	I_D	-2.7 -2.2	A
Pulsed drain current	I_{DM}	-10	A
Power dissipation	P_D	2.3 1.5 1.0 0.7	W
Thermal resistance, junction to ambient	$R_{\theta JA}$	120	$^\circ\text{C}/\text{W}$
Junction and storage temperature range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (at $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Static Parameters						
Drain-source breakdown voltage	BV_{DSS}	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = -250\mu\text{A}$	-30			V
Zero gate voltage drain current	$I_{\text{DS}}^{\text{SS}}$	$V_{\text{DS}} = -30\text{V}, V_{\text{GS}} = 0\text{V}$			-1	μA
Gate-body leakage	I_{GS}	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 20\text{V}$			± 100	nA
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = -250\mu\text{A}$	-1		-3	V
On-state drain current	$I_{\text{D}(\text{on})}$	$V_{\text{DS}} = -5\text{V}, V_{\text{GS}} = -10\text{V}$	-10			A
Static drain-source on resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = -10\text{V}, I_{\text{D}} = -1.9\text{A}$		158	190	$\text{m}\Omega$
		$V_{\text{GS}} = -4.5\text{V}, I_{\text{D}} = -1.4\text{A}$		275	330	
Drain-source diode forward voltage	V_{SD}	$I_{\text{S}} = -1.5\text{A}, V_{\text{GS}} = 0\text{V}$		-0.8	-1.2	V
Forward transconductance	g_{FS}	$V_{\text{DS}} = -5\text{V}, I_{\text{D}} = -1.9\text{A}$		2		S
Max. body-diode continuous current	I_{S}				-1.75	A
Dynamic Characteristics						
Input capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = -15\text{V}, f = 1\text{MHz}$		155		pF
Output capacitance	C_{oss}			35		
Reverse transfer capacitance	C_{rss}			25		
Gate resistance	R_{G}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 0\text{V}, f = 1\text{MHz}$		4	8	Ω
Switching Characteristics						
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = -15\text{V}, R_{\text{L}} = 10\Omega, I_{\text{DS}} = -1.5\text{A}, V_{\text{GEN}} = -10\text{V}, R_{\text{G}} = 1\Omega$		4	8	nS
Rise time	t_{r}			11	18	
Turn-off delay time	$t_{\text{d}(\text{off})}$			11	18	
Fall time	t_{f}			8	18	
Total gate charge	Q_{g}	$V_{\text{GS}} = -15\text{V}, V_{\text{DS}} = -10\text{V}, I_{\text{D}} = -1.9\text{A}$		15.5	22	nC
		$V_{\text{GS}} = -15\text{V}, V_{\text{DS}} = -4.5\text{V}, I_{\text{D}} = -1.9\text{A}$		2	4	
Gate-source charge	Q_{gs}			0.6		
Gate-drain charge	Q_{gd}			1		
Body diode reverse recovery time	t_{rr}	$I_{\text{F}} = -1.5\text{A}, dI/dt = 100\text{A}/\mu\text{s}$		17	26	nS
Body diode reverse recovery charge	Q_{rr}			7		nC

Company reserves the right to improve product design , functions and reliability without notice.

REV:A

Rating and Characteristic Curves (ACMSP2303T-HF)

Fig.1 - Output Characteristics

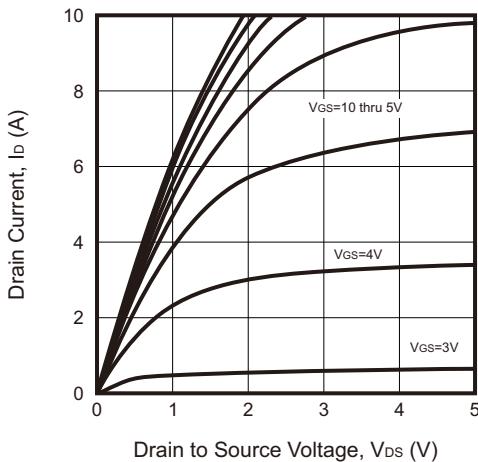


Fig.2 - Transfer Characteristics

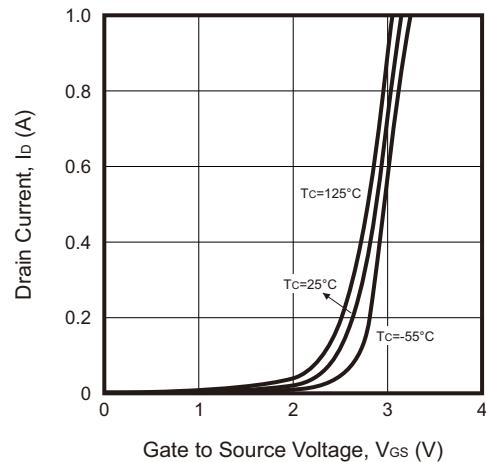


Fig.3 - On-Resistance vs. Drain Current and Gate Voltage

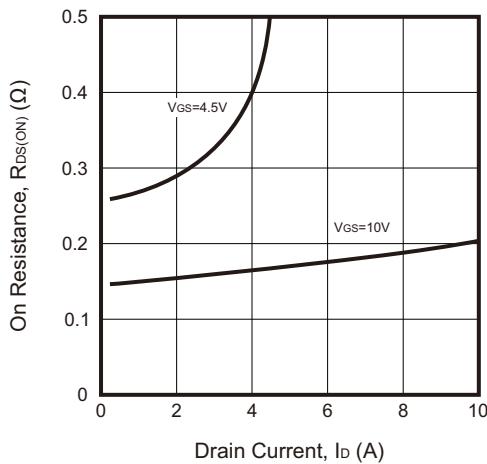


Fig.4 - Capacitance

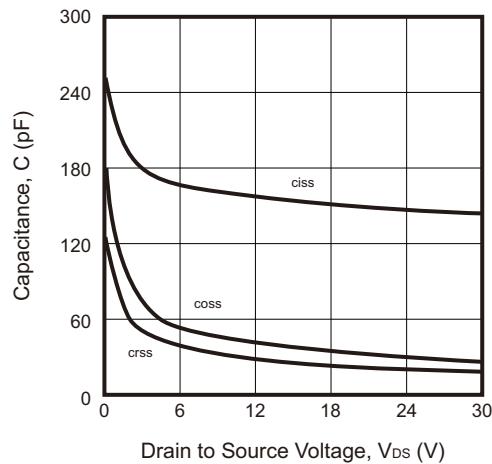


Fig.5 - Gate Charge

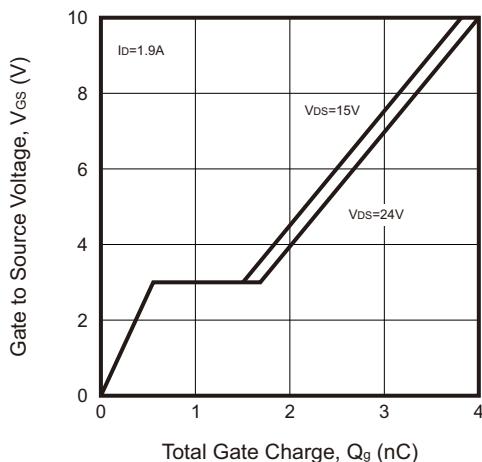
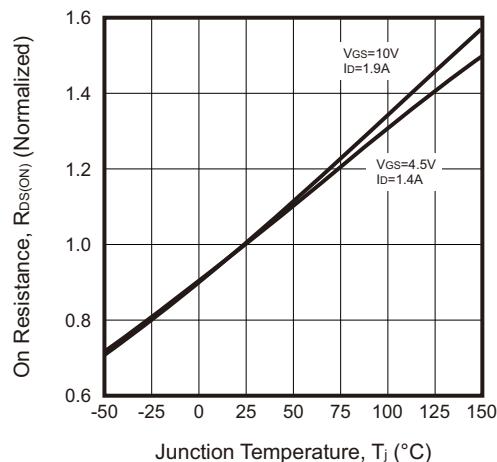


Fig.6 - On-Resistance vs. Junction Temperature



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Rating and Characteristic Curves (ACMSP2303T-HF)

Fig.7 - Source Drain Diode Forward Voltage

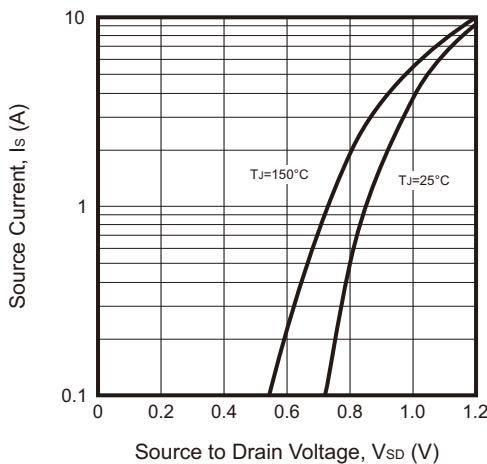


Fig.8 - On-Resistance vs. Gate to Source Voltage

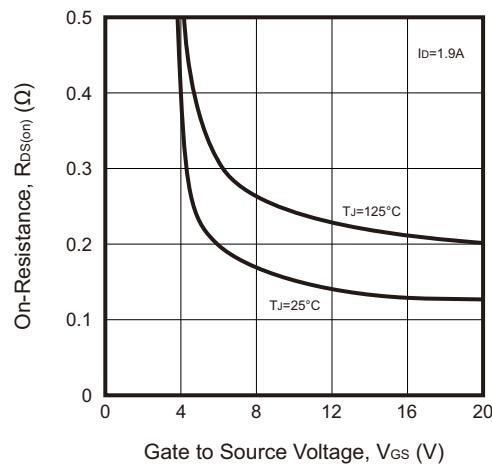


Fig.9 - Threshold Voltage

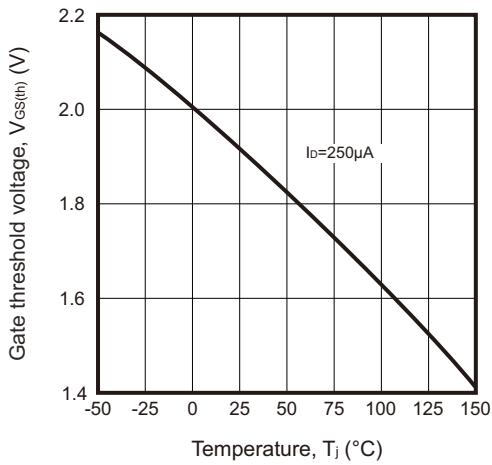
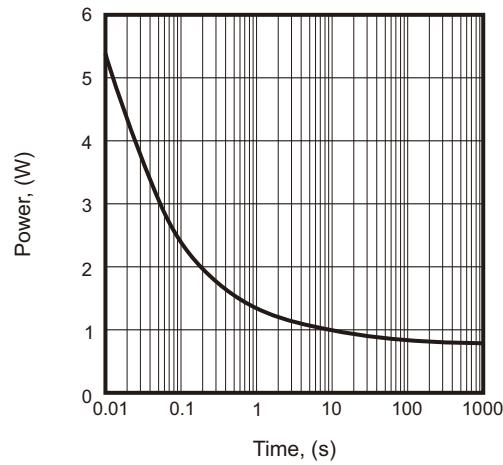
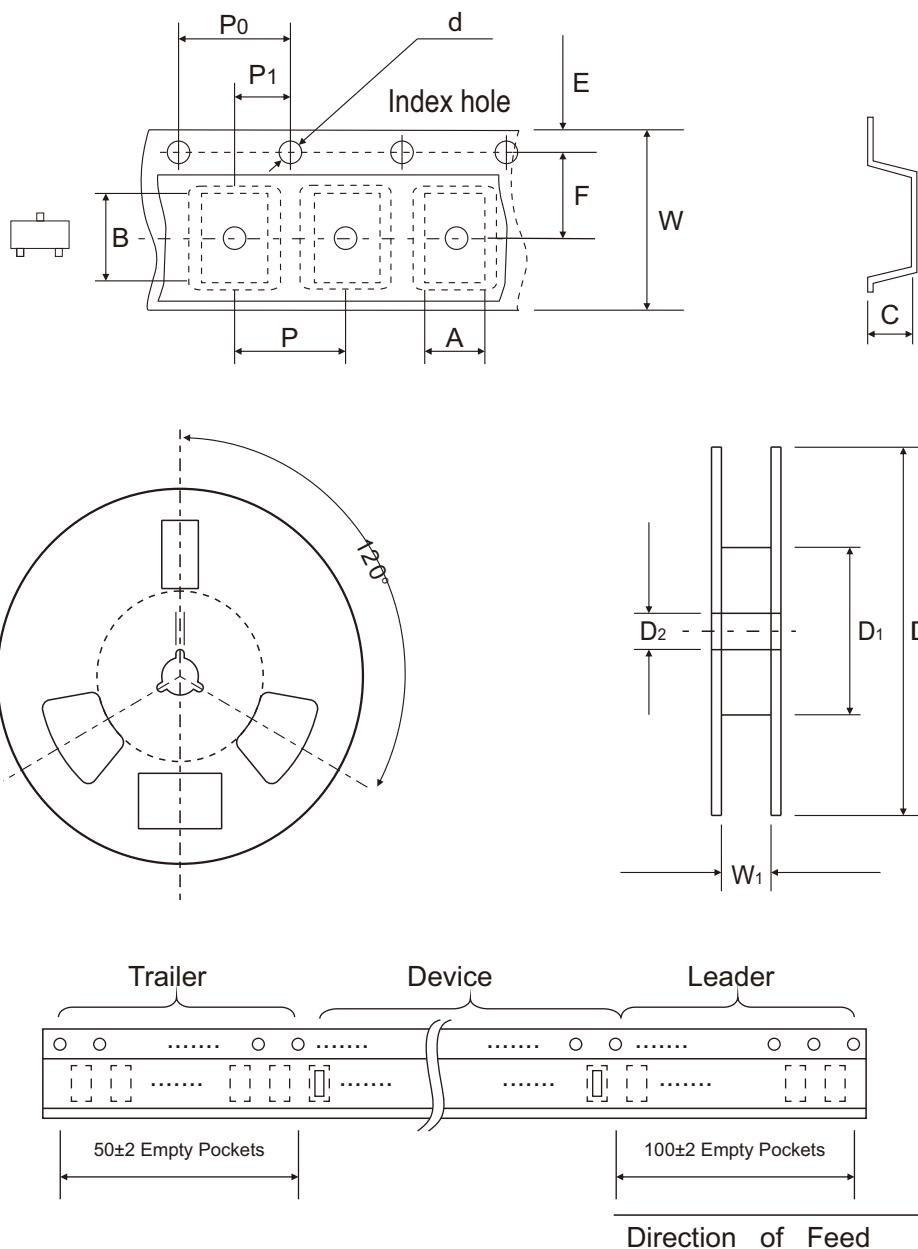


Fig.10 - Single Pulse Power



Reel Taping Specification



	SYMBOL	A	B	C	d	D	D1	D2
SOT-23	(mm)	3.15 ± 0.10	2.77 ± 0.10	1.22 ± 0.10	1.50 ± 0.10	178.00 ± 1.00	54.00 ± 0.50	13.00 ± 0.50
SOT-23	(inch)	0.124 ± 0.004	0.109 ± 0.004	0.048 ± 0.004	0.059 ± 0.004	7.008 ± 0.039	2.126 ± 0.020	0.512 ± 0.020

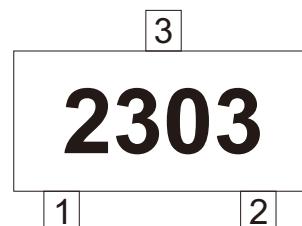
	SYMBOL	E	F	P	P0	P1	W	W1
SOT-23	(mm)	1.75 ± 0.10	3.50 ± 0.05	4.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.05	8.00 ± 0.30 -0.10	9.50 ± 1.00
SOT-23	(inch)	0.069 ± 0.004	0.138 ± 0.002	0.157 ± 0.004	0.157 ± 0.004	0.079 ± 0.002	0.315 ± 0.012 -0.004	0.374 ± 0.039

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REV:A

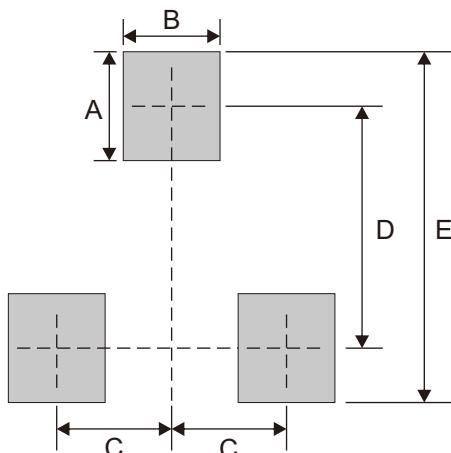
Marking Code

Part Number	Marking Code
ACMSP2303T-HF	2303



Suggested PAD Layout

SIZE	SOT-23	
	(mm)	(inch)
A	0.90	0.035
B	0.80	0.031
C	0.95	0.037
D	2.00	0.079
E	2.90	0.114



Note: 1. The pad layout is for reference purposes only.

Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
SOT-23	3,000	7

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